FAN1110-F085

Advance Information Ignition Module Drive IC

Description

The FAN1110–F085 is designed to directly drive an ignition IGBT and control the current and spark event of the coil. The coil current is controlled via the input pin. When the differential input is driven high, the output of the FAN1110–F085 is enabled to turn on the IGBT and start charging the coil.

An input spike filter suppresses differential input signals of less than 13 µsec in duration. A Max Dwell timer is included in the FAN1110–F085 which will turn off the IGBT if the input stays active for longer than the programmed time. This time interval can be modified through an external capacitor. When the Max Dwell timer is exceeded, the FAN1110–F085 will enter a Hard–Shut–Down mode (HSD) turn off the ignition IGBT immediately. The FAN1110–F085 will also limit the collector current of the IGBT to $I_{C(lim)}$ during charging. This again is done through the sense resistor in the emitter leg of the Ignition IGBT developing a signal input to the V_{SENSE} pin of the FAN1110–F085.

Features

- Differential Input for Ground Shift Disturbances Suppression
- Signal Line Input Buffer
- Input Spike Filter
- Operation from Ignition or Battery Line
- Ground Shift Tolerance –2 V to 3 V
- Programmable Maximum Dwell Time
- Control IGBT Current Limiting through VSENSE Pin
- Hard Shutdown Following Max Dwell Time Out

Applications

The FAN1110–F085 is an advanced Ignition IGBT control IC available in a SO8 package or die sales. This full featured Smart Ignition IGBT Driver is particularly advantageous in "switch on coil" applications where size and system performance of the ignition driver are important.



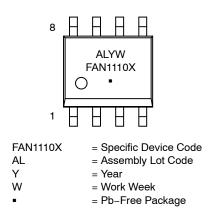
ON Semiconductor®

www.onsemi.com



SOIC8 CASE 751EB

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

ORDERING INFORMATION

Operating Part Number Temperature Range		Package	Packing Method
FAN1110-F085	–40°C to 150°C	8-SOIC	Tape & Reel

Recommended External Components

TYPICAL EXTERNAL COMPONENTS

Component	Description	Vendor	Parameter	Тур.	Unit
R _{BAT}	Limits transient currents during load dump		R	200 to 300	Ω
C _{BAT1}	Battery or Ignition voltage filtering		С	0.47	μF
C _{BAT2}	Battery noise transients		С	10	nF
C _{IN}	Noise immunity		С	10	nF
CINH	Differential mode Noise immunity		С	1	nF
C _{INL}	Differential mode Noise immunity		С	1	nF
R _{SENSE}	Sense the collector current		R	20	mΩ
R _{IN}	Adjust input impedance				

Typical Application

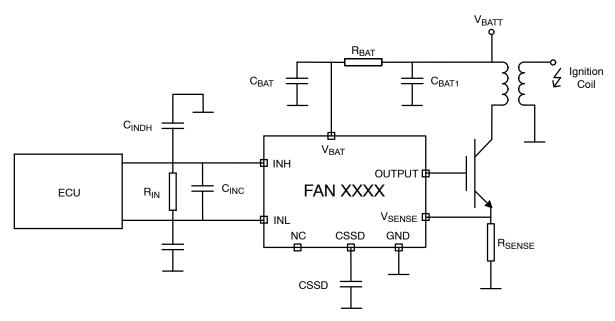
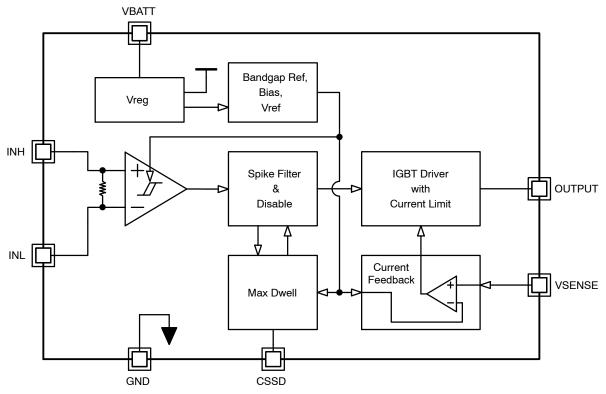


Figure 1. Typical Application

Block Diagram





Package Outline:

The FAN1110–F085 is assembled in an 8 lead SOIC Package.

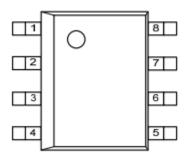


Figure 3. Pin Assignment (Top View)

PIN DESCRIPTION

Name	Туре	Description
Pin1	GND	Ground Reference of the Control IC
Pin2	INL	Input ground signal
Pin3	INH	Positive input signal referenced to INL
Pin4	CSSD	Adjust maximum dwell time (to external capacitor)
Pin5	NC	
Pin6	Output	Gate Drive to the IGBT
Pin7	V _{SENSE}	Sense Input used for Ilim function
Pin 8	V _{BAT}	Supply voltage

ABSOLUTE MAXIMUM RATINGS (-40°C to 150°C Unless Otherwise Stated)

Symbol	Parameter	Min.	Max.	Unit
V _{BAT}	Voltage at V _{bat} pin (excl. EMC transients)	-0.3	28	V
V _{INH}	Voltage at Input pin High	-5	18	V
V _{INL}	Voltage at Input pin Low	-5	18	V
V _{CSSD}	Voltage at C _{SSD}	-0.3	5	V
V _{OUTPUT}	Voltage at Gate Output	-0.3	6.5	V
V _{SENSE}	Voltage on Vsense pin	0	400	mV
T _J , T _{STG}	Operating and Storage Temperature Range	-40	150	°C
P _{MAX}	Maximum power dissipation (continuous) at $T_{C} = 25^{\circ}C$		0.625	W
$R_{ ext{ heta}JA}$	Thermal Resistance junction-case (typical)		200	°C /W
V_{ESD1} (pin to pin excl. V_{INH} and $V_{INL})$	Electrostatic Discharge Voltage (Human Body Model) according to MIL STD 883D, method 3015.7 and EOS/ ESD Assn. standard S5.1 – 1993		2	kV
V_{ESD2} (pin to pin incl. V_{INH} and V_{INL}	Electrostatic Discharge Voltage (Human Body Model) according to MIL STD 883D, method 3015.7 and EOS/ ESD Assn. standard S5.1 – 1993		1.25	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

FAN1110-F085

RECOMMENDED OPERATING CONDITIONS (Reference Load Characteristics) (Note 1)

Symbol	Characteristic	Min.	Тур.	Max.	Units
I _{Ctyp}	Collector (Coil) Operating Current		12		А
Lp	Coil Primary Inductance		1.5		mH
R _P	Coil Primary Resistance (25°C)		0.4		Ω
R _{LOAD}	Load Resistance (for delay time measurements)		2		Ω

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

1. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings. (-40°C to 150°C unless otherwise stated).

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
POWER SUP	PLY CONDITIONS V _{BAT} = 6 to 28 \	/ ; $T_J = -40^{\circ}C$ to 150°C (unless otherwise speci	fied)			
V _{BAT1}	Operating voltage	Coil switching function	4		28	V
V _{BAT2}	Operating voltage	All functions	6		28	V
I _{BAT}	Supply current	TJ=150 °C, Vbat = 28 V, Input = 5 V			4	mA
VCLAMP	V _{BATTERY} clamp	lbatt = 10 mA	35		50	V
SENSE PIN C	CONDITIONS VBAT = 6 to 28 V ; T	$_{J}$ = -40°C to 150 °C (unless otherwise specified)				
V _{LIMIT}	Sense Voltage at current limit		200	220	240	mV
T _{SPIKE}	Input spike filter	Delay on rising and falling edge of Input		13		μs
T _{D1}	Turn on delay time	(Time from Input = 4.0 V to V _{OUT} = 4.0 V)		17		μs
T _{D2}	Turn off delay time	(Time from Input = 0.5 V to V_{C-GND} = 1.0 V)		17		μs
INPUT CONTI	ROL CONDITIONS V _{BAT} = 6 to 28	V; $T_J = -40^{\circ}C$ to + 150°C (unless otherwise spe	cified)			
V _{INLD}	Differential Input low voltage	INL = GND	1.4	1.9	2.4	V
V _{INHD}	Differential Input high voltage	INL = GND	1.8	2.5	3.1	V
V _{INHys}	Input voltage hysteresis		0.3	0.6	0.9	V
I _{IN}	Input current	V _{BAT} = 0V, INL= GND		0.33×V _{INH}		mA
I _{IN}	Input current	6 V < V _{BAT} < 20 V, INL = GND		0.10×V _{INH}		mA
V _{CM}	Common mode voltage	between V_{INH} and V_{INL} reference to GND	-2		3	V
V _{INHGF}	Floating INH voltage	(6 V < VS < 20 VINH and INL floating) refer to GND @ T = 25°C		0.8		V
V _{INLGF}	Floating INL voltage	(6 V < VS < 20 VINH and INL floating) refer to GND @ T = 25°C		0.8		V

GATE OUTPUT VOLTAGE MAX V_{BAT} = 6 to 28 V ; T_J = -40°C to 150°C (unless otherwise specified)

V _{GMAX}	Vgate max	16 K Ω pulldown resistor	4.5	5.25	6	V
V _{GLOW}	Vgate low	(0 mA < I_{GATE} < 0.4 mA @ T = 25°C)	0.0		0.2	V

DIAGNOSTIC FUNCTIONS AND PROTECTION $V_{BAT} = 6$ to 28 V ; $T_J = -40^{\circ}C$ to 150°C (unless otherwise specified)

CSSD _{MIN}	Minimum dwell time capacitor			5		nF
TD _{MAX}	Maximum dwell time	(CSSD = 50 nF)	65	100	135	ms
I _{CSSD1}	CSSD Pin current for TDMAX		0.8	1.25	1.5	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

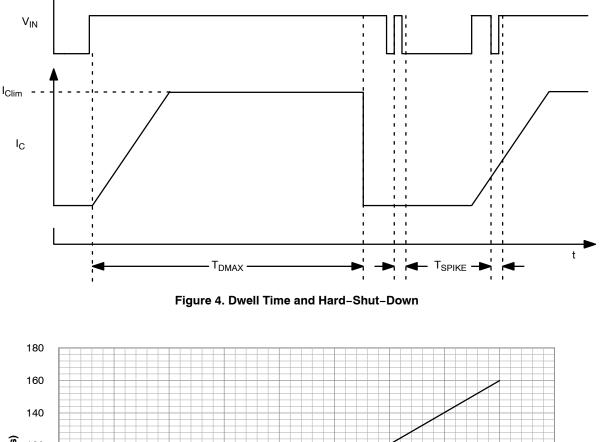
TYPICAL PERFORMANCE CHARACTERISTICS

Input and Spike Filter

When the differential input signal voltage between INH and INL pins reaches V_{INHD} , the IGBT will be switched on charging the coil. When this differential input voltage goes below V_{INLD} , the coil current through the IGBT will be turned off. Positive and negative spikes of less than T_{SPIKE} duration at the input line will be filtered out and will not turn on/off the IGBT.

Maximum Dwell Time and Hard-Shutdown (HSD)

When the IGBT is turned on, a delay timer, dependent on the value of the external CSSD capacitor (see Fig. 5), is started. If a valid falling edge has not been received after the time T_{DMAX} , the IGBT will be turned off immediately as shown in Fig. 4.



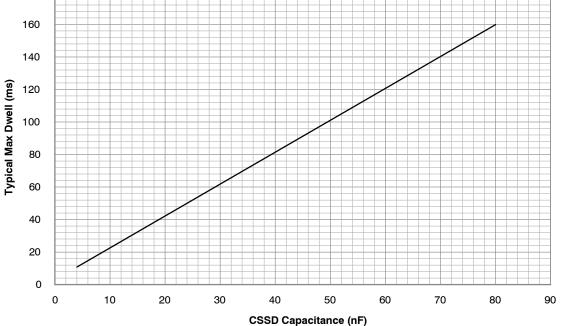
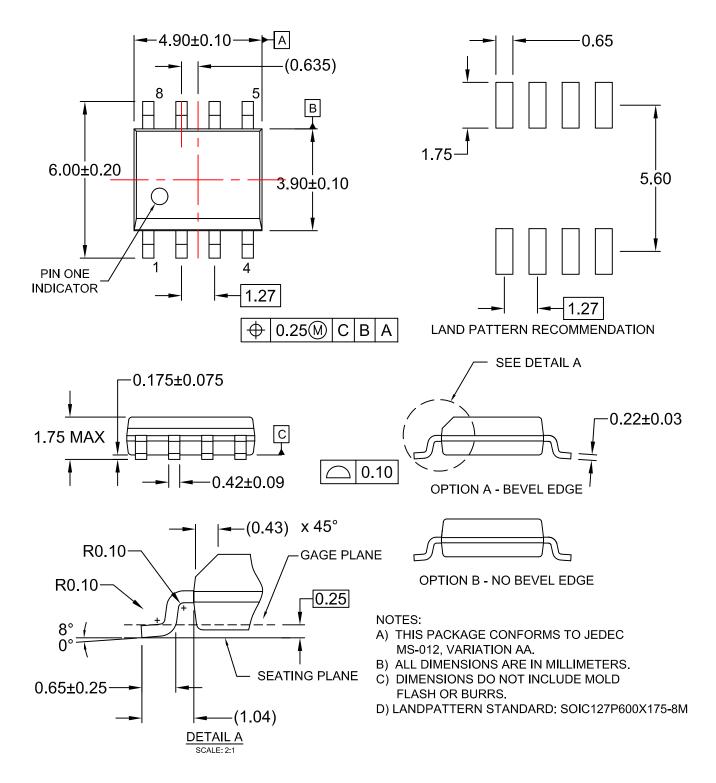


Figure 5. $T_{\mbox{\scriptsize DMAX}}$ as Function of External CSSD Capacitor

PACKAGE DIMENSIONS





FAN1110-F085

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconducts harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death

Phone: 421 33 790 2910

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative